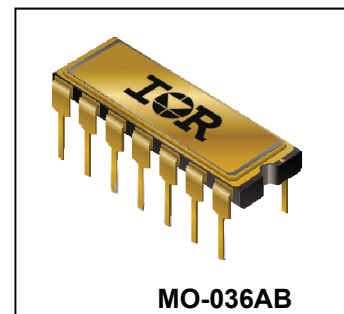


**POWER MOSFET
THRU-HOLE (MO-036AB)**
100V, QUAD P-CHANNEL
REF: MIL-PRF-19500/599
HEXFET® MOSFET TECHNOLOGY
Product Summary

Part Number	RDS(on)	I _D
IRFG9110	1.4Ω	-0.75A

Description

HEXFET® MOSFET technology is the key to IR HiRel advanced line of power MOSFET transistors. The efficient geometry design achieves very low on-state resistance combined with high trans conductance. HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and electrical parameter temperature stability. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, high energy pulse circuits, and virtually any application where high reliability is required. The HEXFET transistor's totally isolated package eliminates the need for additional isolating material between the device and the heatsink. This improves thermal efficiency and reduces drain


Features

- Simple Drive Requirements
- Hermetically Sealed
- Electrically Isolated
- Dynamic dv/dt Rating
- Light Weight

Absolute Maximum Ratings (Per Die)

Symbol	Parameter	Value	Units
I _{D1} @ V _{GS} = -10V, T _C = 25°C	Continuous Drain Current	-0.75	A
I _{D2} @ V _{GS} = -10V, T _C = 100°C	Continuous Drain Current	-0.5	
I _{DM} @ T _C = 25°C	Pulsed Drain Current ①	-3.0	
P _D @ T _C = 25°C	Maximum Power Dissipation	1.4	W
	Linear Derating Factor	0.011	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy ②	75	mJ
I _{AR}	Avalanche Current ①	-0.75	A
E _{AR}	Repetitive Avalanche Energy ①	0.14	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.5	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 (0.063 in. /1.6 mm from case for 10s)	
	Weight	1.3 (Typical)	g

For Footnotes, refer to the page 2.

Electrical Characteristics For Each P-Channel Device @ T_J = 25°C (Unless Otherwise Specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V _{GS} = 0V, I _D = -1.0mA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	-0.098	—	V/°C	Reference to 25°C, I _D = -1.0mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	1.4	Ω	V _{GS} = -10V, I _{D1} = -0.5A ④
		—	—	1.73		V _{GS} = -10V, I _{D1} = -0.75A ④
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -250μA
G _{fs}	Forward Transconductance	0.67	—	—	S	V _{DS} = -15V, I _{D2} = -0.5A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-25	μA	V _{DS} = -80V, V _{GS} = 0V
		—	—	-250		V _{DS} = -80V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -20V
	Gate-to-Source Leakage Reverse	—	—	100		V _{GS} = -20V
Q _G	Total Gate Charge	—	—	15	nC	I _{D1} = -0.75A
Q _{GS}	Gate-to-Source Charge	—	—	7.0		V _{DS} = -50V
Q _{GD}	Gate-to-Drain ('Miller') Charge	—	—	8.0		V _{GS} = -10V
t _{d(on)}	Turn-On Delay Time	—	—	30	ns	V _{DD} = -50V
t _r	Rise Time	—	—	60		I _{D1} = -0.75A
t _{d(off)}	Turn-Off Delay Time	—	—	70		R _G = 7.5Ω
t _f	Fall Time	—	—	80		V _{GS} = -10V
L _S + L _D	Total Inductance	—	10	—	nH	Measured from Drain lead (6mm / 0.25 in from package) to Source lead (6mm / 0.25 in from package) with Source wire internally bonded from Source pin to Drain pin
C _{iss}	Input Capacitance	—	200	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	85	—		V _{DS} = -25V
C _{rss}	Reverse Transfer Capacitance	—	30	—		f = 1.0MHz

Source-Drain Diode Ratings and Characteristics (Per Die)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-0.75	A	
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-3.0		
V _{SD}	Diode Forward Voltage	—	—	-5.5	V	T _J = 25°C, I _S = -0.75A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	200	ns	T _J = 25°C, I _F = -0.75A, V _{DD} ≤ -50V
Q _{rr}	Reverse Recovery Charge	—	—	9.0	μC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Thermal Resistance (Per Die)

Symbol	Parameter	Min.	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	—	17	°C/W
R _{θJA}	Junction-to-Ambient (Typical socket mount)	—	—	90	

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② V_{DD} = -25V, starting T_J = 25°C, L = 266mH, Peak I_L = -0.75A, V_{GS} = -10V
- ③ I_{SD} ≤ -0.75A, di/dt ≤ -75A/μs, V_{DD} ≤ -100V, T_J ≤ 150°C
- ④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%

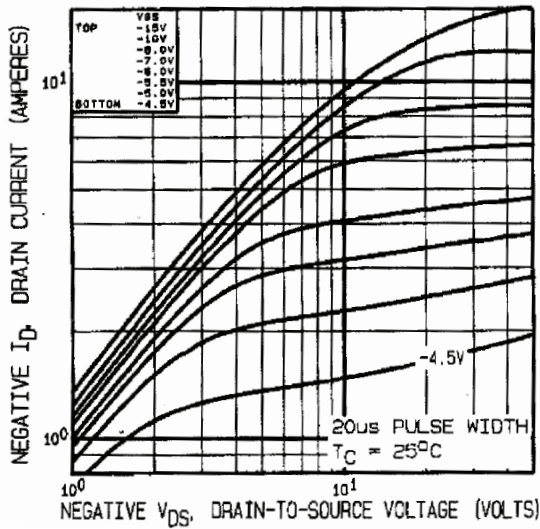


Fig 1. Typical Output Characteristics

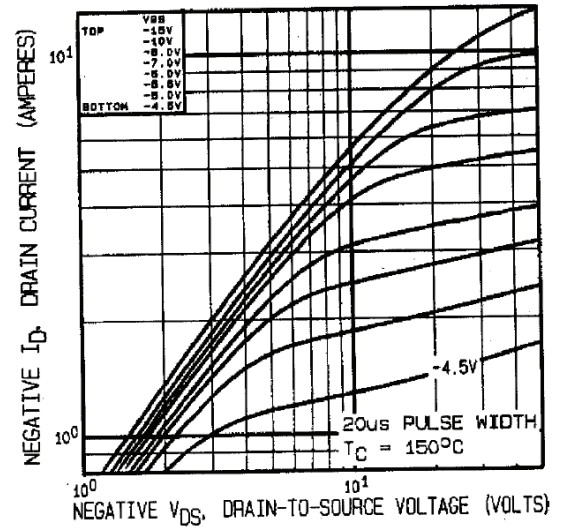


Fig 2. Typical Output Characteristics

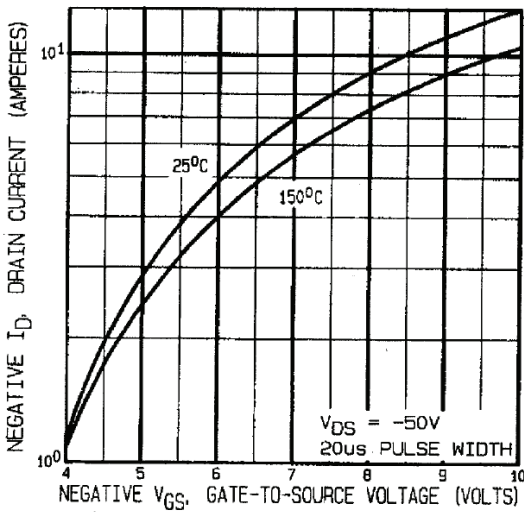


Fig 3. Typical Transfer Characteristics

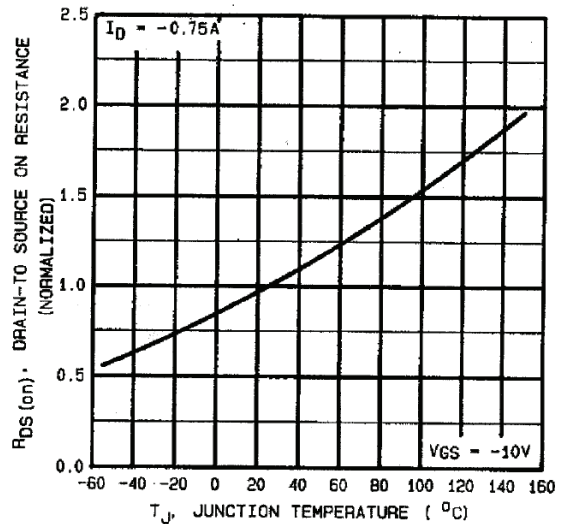


Fig 4. Normalized On-Resistance Vs. Temperature

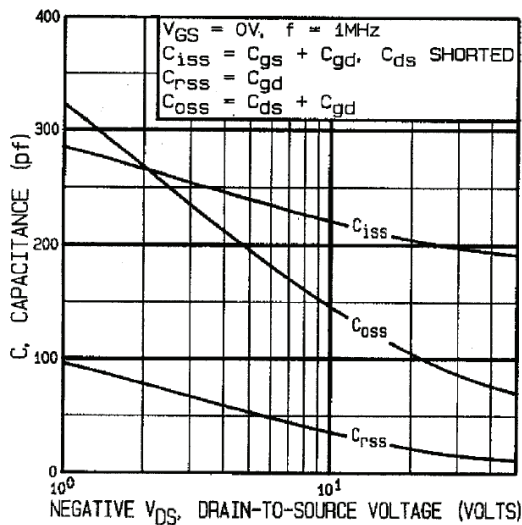


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

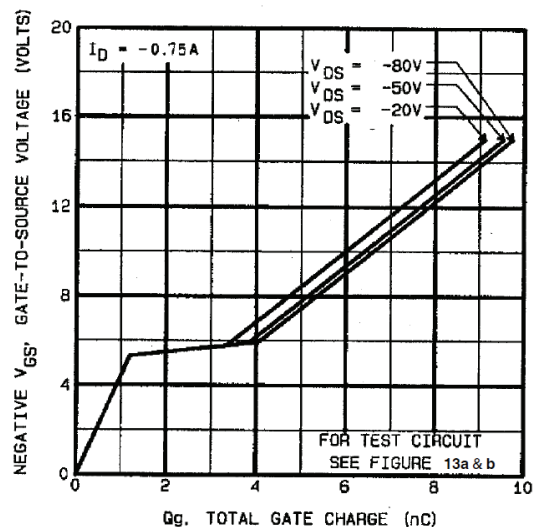


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

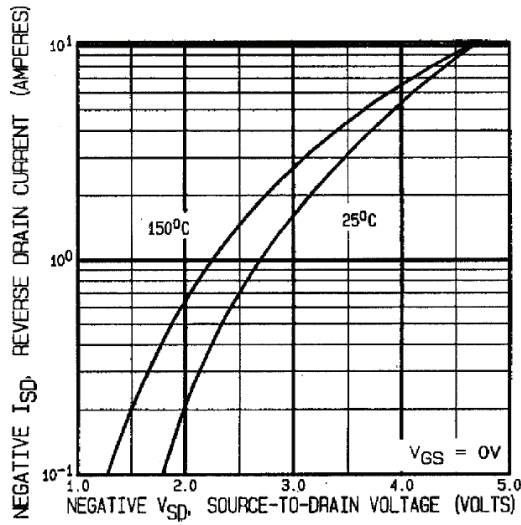


Fig 7. Typical Source-Drain Diode Forward Voltage

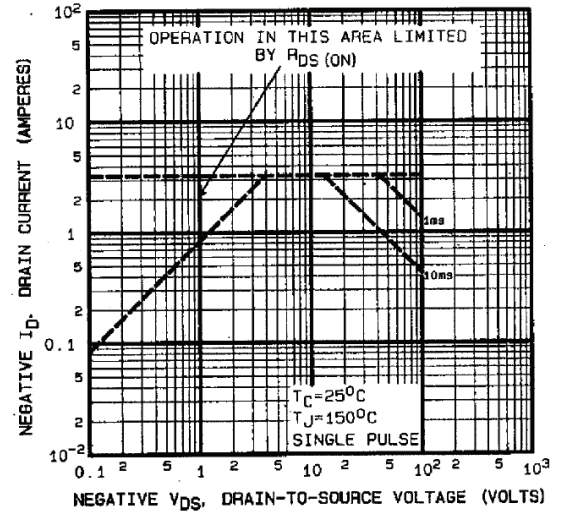


Fig 8. Maximum Drain Current Vs. Case Temperature

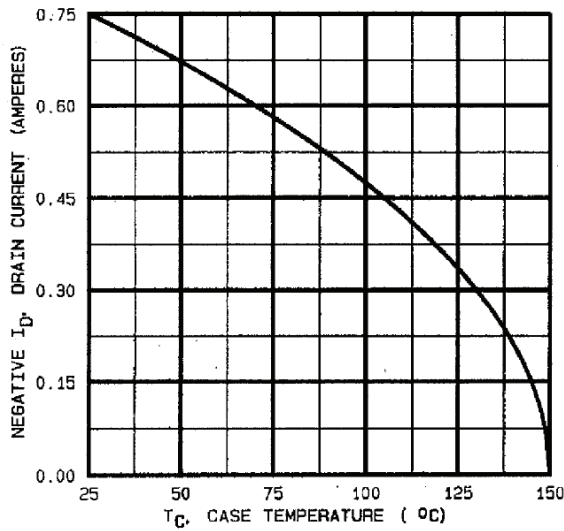


Fig 9. Maximum Drain Current Vs. Case Temperature

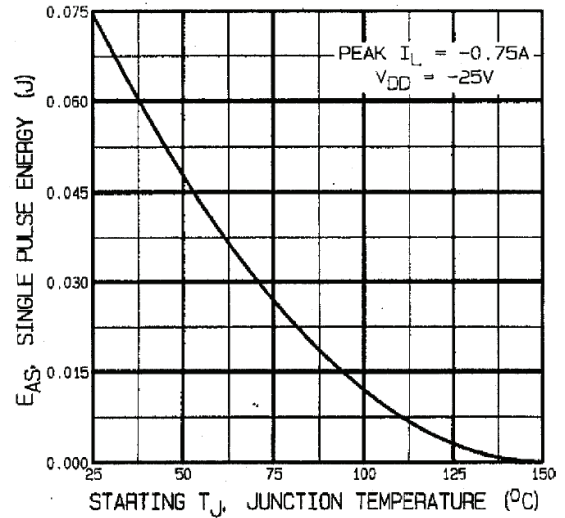


Fig 10. Maximum Avalanche Energy Vs. Drain Current

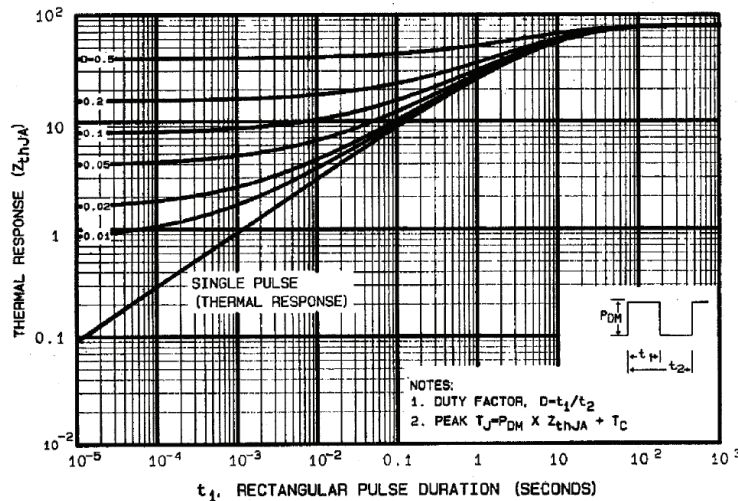


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

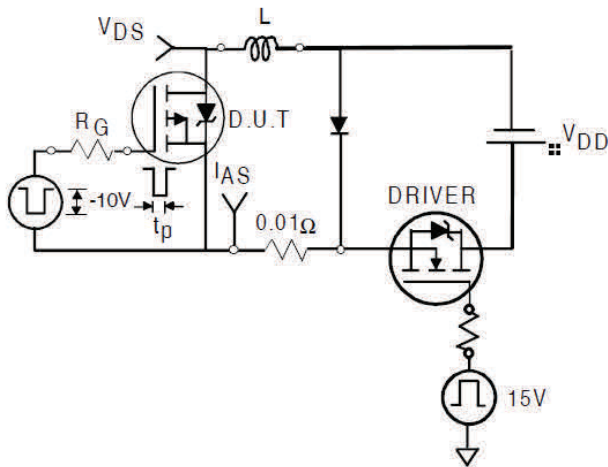


Fig 12a. Unclamped Inductive Test Circuit

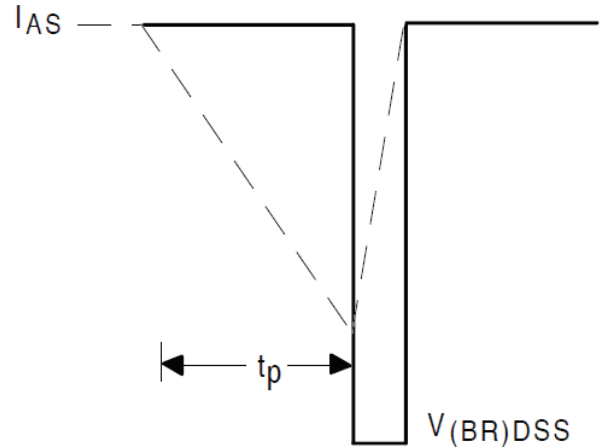


Fig 12b. Unclamped Inductive Waveforms

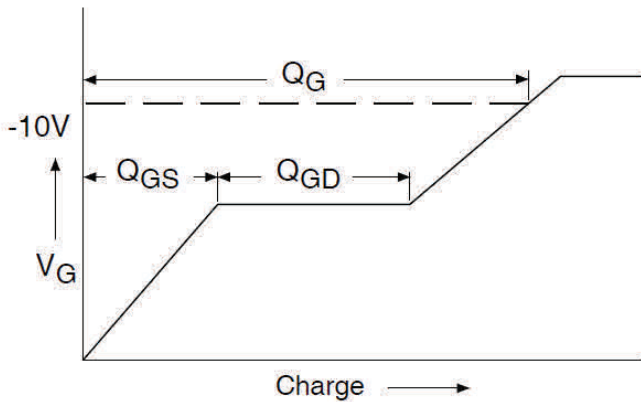


Fig 13a. Gate Charge Waveform

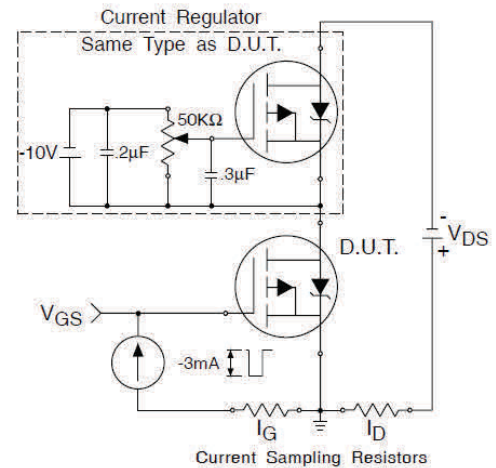


Fig 13b. Gate Charge Test Circuit

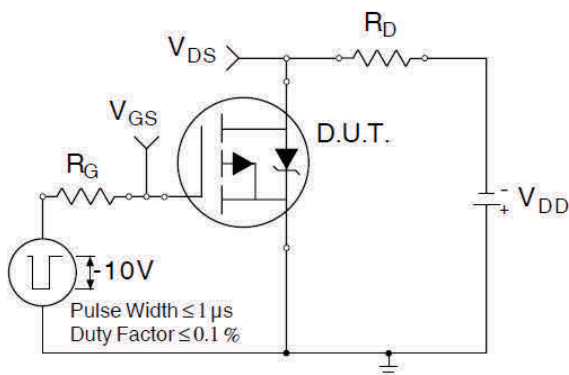


Fig 14a. Switching Time Test Circuit

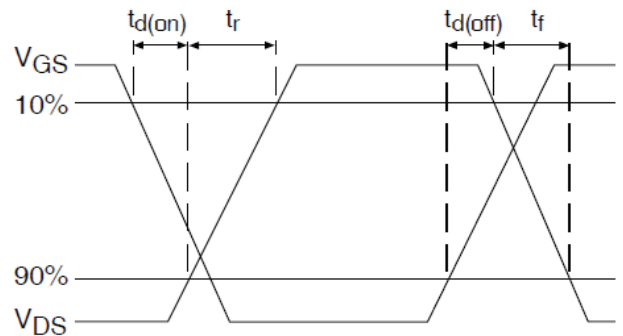
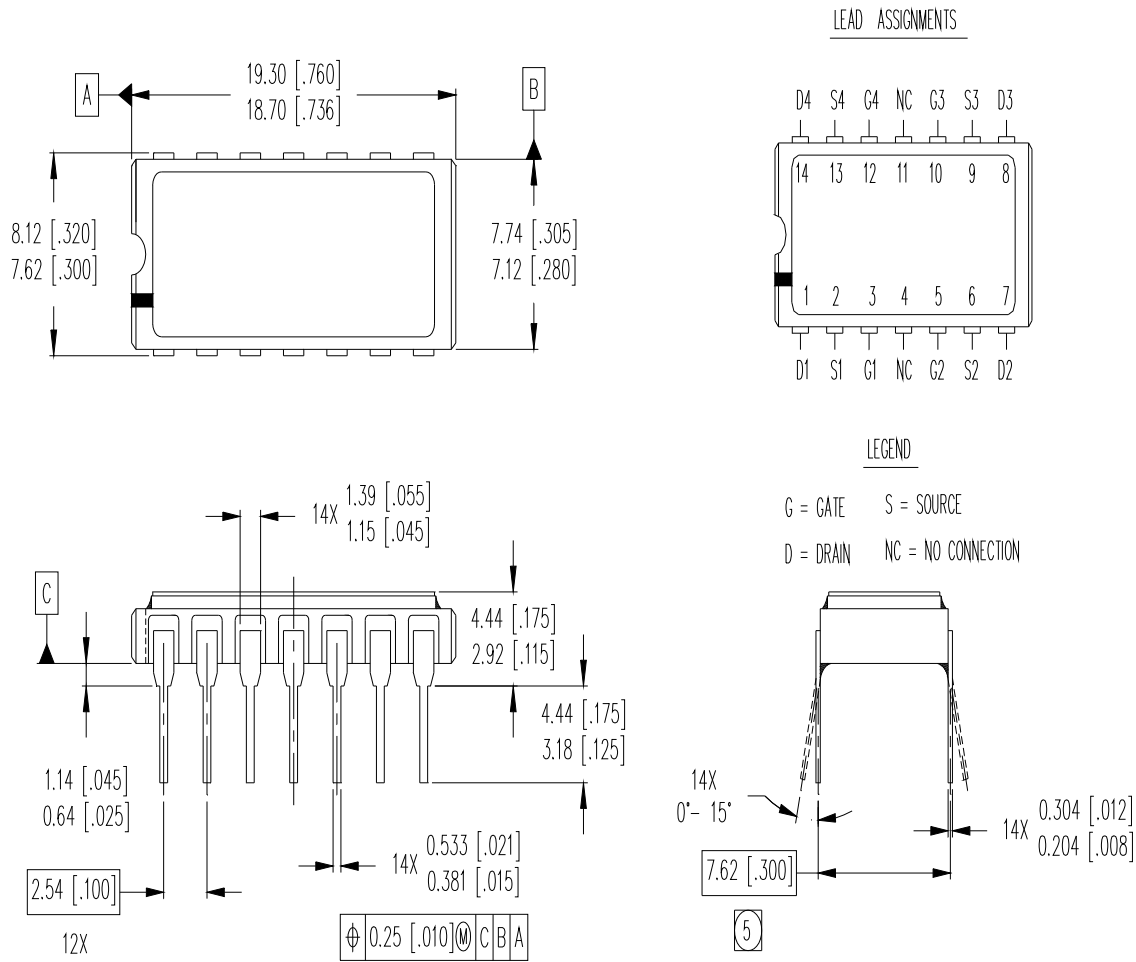


Fig 14b. Switching Time Waveforms

Case Outline and Dimensions - MO-036AB



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 4. OUTLINE CONFORMS TO JEDEC OUTLINE MO-036AB.
- ⑤ MEASURED WITH THE LEADS CONSTRAINED TO BE PERPENDICULAR TO DATUM PLANE C.

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